

IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Previously Presented): A method for processing an organosiloxane film, the method comprising:

loading a target substrate with a coating film formed thereon into a reaction chamber, the coating film comprising a polysiloxane base solution having an organic functional group; and

performing a heat process on the target substrate within the reaction chamber to bake the coating film, wherein the heat process comprises:

a temperature setting step of setting an interior of the reaction chamber at a process temperature by heating, and

a supplying step of supplying a baking gas into the reaction chamber set at the process temperature, while activating the baking gas by a gas activation section disposed outside the reaction chamber, the gas activation section activating the baking gas by bringing the baking gas into contact with a catalyst while supplying the baking gas with heat energy, wherein:

the baking gas is selected from the group consisting of ammonia gas and dinitrogen oxide gas,

the catalyst is tungsten, and

the gas activation section is configured to heat the baking gas to a temperature of from 700 to 1,000°C.

Claim 2 (Original): The method according to claim 1, wherein the process temperature ranges from 250 to 400°C.

Claims 3-16 (Canceled).

Claim 17 (Previously Presented): The method according to claim 1, wherein the reaction chamber is configured to accommodate a plurality of target substrates at intervals in a vertical direction, said loading comprising loading the plurality of target substrates.

Claims 18-21 (Canceled).